**Product data sheet** 

## 1. General description

WeEn's 5th Generation Hyper Fast diode with softer recovery in a 2-lead IITO220 plastic package.

#### 2. Features and benefits

- Isolated mounting base with 2500 V (RMS) isolation
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- · Soft reverse recovery with low recovery current
- · Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- · Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				600		V
$I_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		30			Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 $\mu$ s; square-wave pulse		60			А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		260 286			Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse					А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.00	2.75	V
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	-	45	ns

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode		K — A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020
			U U 1 2 IITO220-2L	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC30Y-600PS	IITO220-2L	BYC30Y-600PSQ	Tube	50	IITO220E-2L	03-Mar-2020

## 7. Marking

#### Table 4. Marking codes

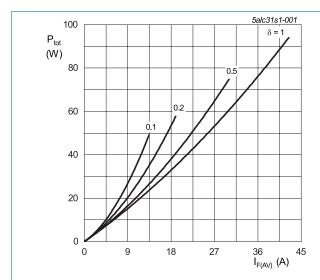
Type number	Marking codes
BYC30Y-600PS	BYC30Y
	600PS

## 8. Limiting values

#### **Table 5. Limiting values**

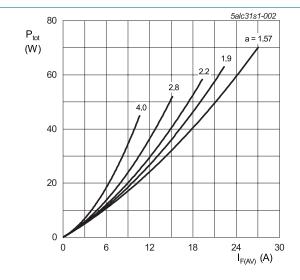
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			600	V
$V_{RWM}$	crest working reverse voltage			600	V
$V_R$	reverse voltage	DC		600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		30	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 µs; square-wave pulse		60	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		260	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		286	Α
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



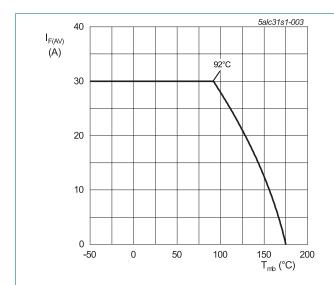
$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.544 \text{ V; } R_s = 0.0158 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.544 V;  $R_s$  = 0.0158  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





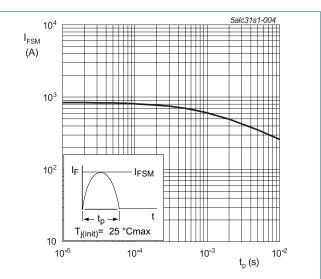
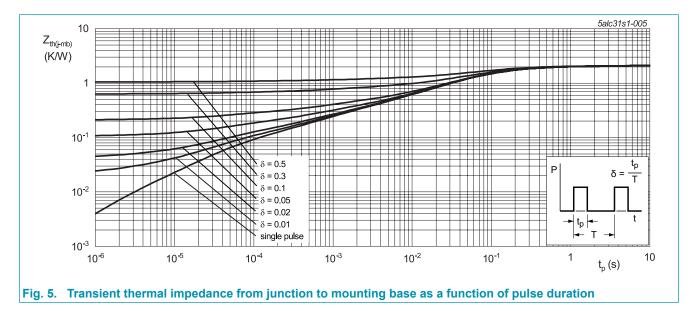


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5		-	-	2.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W



### 10. Isolation characteristics

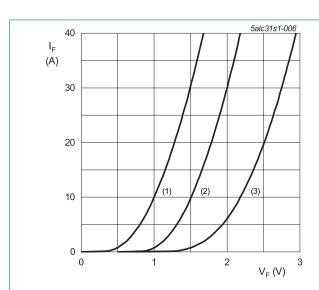
#### **Table 7. Isolation characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

## 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.00	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.50	2.00	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C		-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C		-	-	0.6	mA
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$		-	-	45	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	51	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	105	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	3.7	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	9.5	-	А
$Q_r$	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 \text{ °C}; Fig. 7$		-	95	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$		-	498	-	nC
S <sub>factor</sub>	softness factor	$I_F = 30 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A}/\mu\text{s}$ ; $T_i = 125 \text{ °C}$ ; Fig. 7		-	0.55	-	



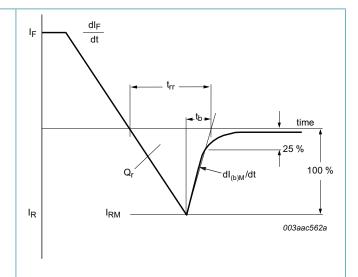
(1) T<sub>i</sub> = 150 °C; typical values

(2) T<sub>i</sub> = 150 °C; maximum values

(3)  $T_j = 25$  °C; maximum values

 $V_o = 1.544 \text{ V}; R_s = 0.0158 \Omega$ 



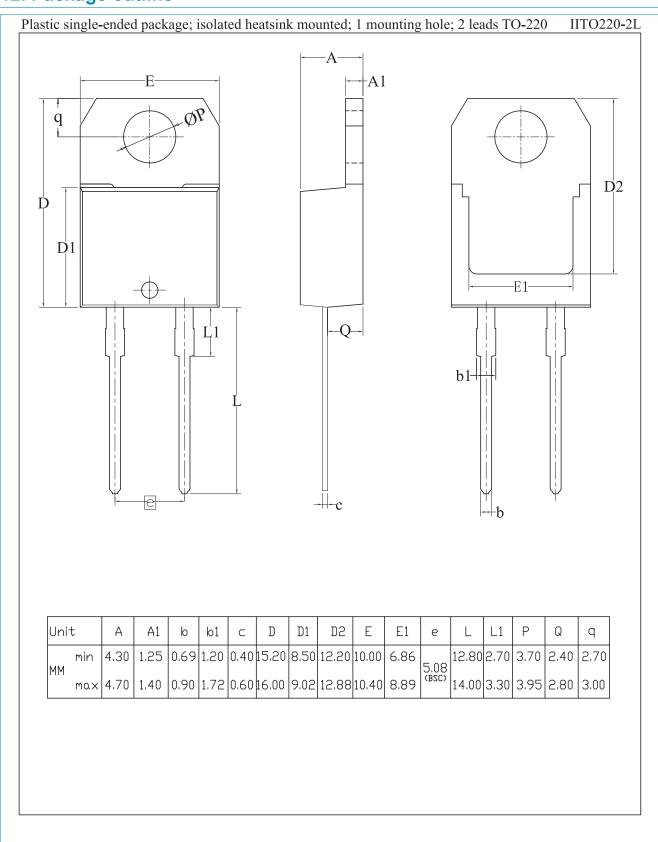


 $S_{factor} = [dI_F/dt] / [dI_{(b)M}/dt]$ 

 $dI_{(b)M}/dt$  = peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 7. Reverse recovery definitions; ramp recovery

## 12. Package outline



### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**BYC30Y-600PS** 

Hyperfast power diode

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Date of release: 26 December 2022

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